ISO654x General Purpose Quad-Channel Functional Isolators

1 Features

- Up to 50Mbps data rate
- Robust SiO₂ isolation barrier
- Functional Isolation (DBQ-16):
 - 400V_{RMS}, 566V_{DC} working voltage
 - 707V_{RMS}, 1000V_{DC} transient voltage (60s)
- Wide temperature range: -40°C to 125°C
- ±150kV/µs typical CMTI
- Supply range: 1.71V to 5.5V
- Default output high (ISO654x) and low (ISO654xF) options
- 1.5mA per channel typical at 1Mbps and 3.3V (ISO6540)
- Low propagation delay: 11ns typical at 3.3V
- Robust electromagnetic compatibility (EMC)
 - System-level ESD, EFT, and surge immunity
 - Low emissions
- SSOP (DBQ-16) Package

2 Applications

- Power supplies
- Grid, electricity meter
- Motor drives
- **Factory automation**
- **Building automation**
- Lighting
- **Appliances**

3 Description

The ISO654x devices are general purpose functional isolators for cost sensitive, space constrained applications that require isolation for non-safety applications. The isolation barrier supports a working voltage of 400V_{RMS} / 566V_{DC} and transient over voltages of $707V_{RMS}$ / $1000V_{DC}$.

The ISO654x devices provide high EMC performance while isolating CMOS or LVCMOS digital I/Os. ISO654x uses SiO₂ as the isolation barrier. Each isolation channel has a logic input and output buffer separated by the insulation barrier. These devices come with enable pins that can be used to put the respective outputs in high impedance.

The ISO6540 and ISO6540F devices have all channels in the forward direction. The ISO6541 and ISO6541F devices have one reverse-direction channel. The ISO6542 and ISO6542F devices have two reverse-direction channels.

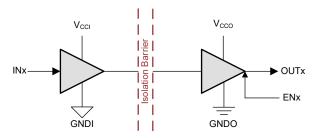
In the event of input power or signal loss, the default output is high for devices without the suffix F and low for devices with the suffix F. See Section 7.4 for further details.

These devices help prevent noise currents on GPIOs or data buses such as SPI, UART RS-485, RS-232, and CAN from causing data corruption or damaging sensitive circuitry. Through chip design and layout techniques, the electromagnetic compatibility of the devices have been significantly enhanced to ease system-level design.

Package Information

PART NUMBER ⁽¹⁾	PACKAGE	PACKAGE SIZE ⁽²⁾
ISO6540 , ISO6540F	SSOP (DBQ-16)	6mm × 4.9mm
ISO6541 , ISO6541F		
ISO6542 , ISO6542F		

- (1) For more information, see Section 11.
- (2)The package size (length × width) is a nominal value and includes pins, where applicable.



V_{CCI}=Input supply, V_{CCO}=Output supply GNDI=Input ground, GNDO=Output ground

Simplified Schematic



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4 Pin Configuration and Functions

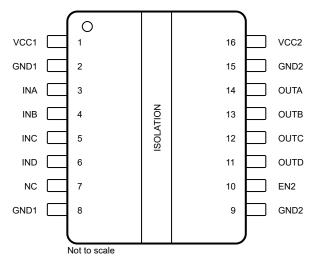


Figure 4-1. ISO6540 and ISO6540F Top View

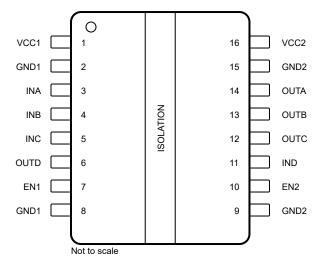


Figure 4-2. ISO6541 and ISO6541F Top View

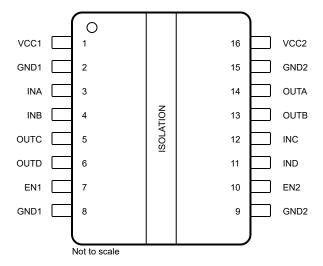


Figure 4-3. ISO6542 and ISO6542F Top View



Table 4-1. Pin Functions

	I	PIN			
NAME	ISO6540 , ISO6540F	ISO6541 , ISO6541F	ISO6542 , ISO6542F	Type ⁽¹⁾	Output enable 1. Output pins on side 1 are enabled when EN1 is high or open and in high-impedance state when EN1 is low. Output enable 2. Output pins on side 2 are enabled when EN2 is high or open and in high-impedance state when EN2 is low. Ground connection for V _{CC1} Ground connection for V _{CC2} I Input, channel A I Input, channel B I Input, channel C I Input, channel D Not connected O Output, channel A O Output, channel B O Output, channel B
EN1	-	7	7	1	Output enable 1. Output pins on side 1 are enabled when EN1 is high or open and in high-impedance state when EN1 is low.
EN2	10	10	10	I	Output enable 2. Output pins on side 2 are enabled when EN2 is high or open and in high-impedance state when EN2 is low.
GND1	2, 8	2,8	2,8	_	Ground connection for V _{CC1}
GND2	9, 15	9,15	9,15	_	Ground connection for V _{CC2}
INA	3	3	3	I	Input, channel A
INB	4	4	4	I	Input, channel B
INC	5	5	12	ı	Input, channel C
IND	6	11	11	I	Input, channel D
NC	7	-	-		Not connected
OUTA	14	14	14	0	Output, channel A
OUTB	13	13	13	0	Output, channel B
OUTC	12	12	5	0	Output, channel C
OUTD	11	6	6	0	Output, channel D
V _{CC1}	1	1	1	_	Power supply, side 1
V _{CC2}	16	16	16	_	Power supply, side 2

⁽¹⁾ I = Input, O = Output



5 Specifications

5.1 Absolute Maximum Ratings

See⁽¹⁾

		MIN	MAX	UNIT
Supply voltage (2)	V _{CC1} to GND1	-0.5	6	V
Supply voltage (-/	V _{CC2} to GND2	-0.5	6	V
Input/Output	INx to GNDx	-0.5	V _{CCX} + 0.5 ⁽³⁾	V
Voltage	OUTx to GNDx	-0.5	V _{CCX} + 0.5 ⁽³⁾	V
Output current	lo	-15	15	mA
Tomporatura	Operating junction temperature, T _J		150	°C
Temperature	Storage temperature, T _{stg}	-65	150	°C
Transient	AC Voltage, t=60s		707	V _{RMS}
Isolation Voltage (SSOP-16)	DC Voltage, t=60s		1000	V _{DC}

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values
- (3) Maximum voltage must not exceed 6V.

5.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ ESDA/JEDEC JS-001, all pins ⁽¹⁾	±6000	
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC1} (1)	Supply Voltage Side 1	V _{CC} = 1.8V ⁽³⁾	1.71		1.89	V
V _{CC1} (1)	Supply Voltage Side 1	V _{CC} = 2.5V to 5V ⁽³⁾	2.25		5.5	V
V _{CC2} (1)	Supply Voltage Side 2	V _{CC} = 1.8V ⁽³⁾	1.71		1.89	V
V _{CC2} (1)	Supply Voltage Side 2	$V_{CC} = 2.5V \text{ to } 5V^{(3)}$	2.25		5.5	V
	UVLO threshold when supply vo	oltage is rising		1.53	1.71	V
	UVLO threshold when supply vo	oltage is falling	1.1	1.41		V
	Supply voltage UVLO hysteresis	s	0.08	0.13		V
/ _{IH}	High level Input voltage		0.7 × V _{CCI}		V _{CCI}	V
/ _{IL}	Low level Input voltage		0	(0.3 × V _{CCI}	V
(UVLO+) Vcc (UVLO-) Vhys (UVLO) VIH VIL		V _{CCO} = 5V ⁽²⁾	-4			mA
	High lavel autout august	V _{CCO} = 3.3V	-2			mA
ОН	High level output current	V _{CCO} = 2.5V	-1			mA
		V _{CCO} = 1.8V	-1			mA
		V _{CCO} = 5V		5.5 1.53 1.71 1.41 0.13 V _{CCI} 0.3 × V _{CCI} 4 2 1 50 25 125 400	4	mA
Vcc (UVLO+) Vcc (UVLO-) Vhys (UVLO) V _{IH} V _{IL} I _{OH}	Lauria val autout aumant	V _{CCO} = 3.3V			2	mA
	Low level output current	V _{CCO} = 2.5V			1	mA
		V _{CCO} = 1.8V			1	mA
DR	Data Rate	.	0		50	Mbps
ΓΑ	Ambient temperature		-40	25	125	°C
V _{IH} V _{IL} I _{OH} I _{OL} DR T _A	Functional Isolation Working	AC Voltage (sine wave)			400	V _{RMS}
ΙA	Voltage (SSOP-16)	DC Voltage			566	V_{DC}

 ⁽¹⁾ V_{CC1} and V_{CC2} can be set independent of one another
 (2) V_{CC1} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}
 (3) The channel outputs are in undetermined state when 1.89V < V_{CC1}, V_{CC2} < 2.25V and 1.05V < V_{CC1}, V_{CC2} < 1.71V



5.4 Thermal Information

		ISO654x	
	THERMAL METRIC(1)	DBQ (SSOP)	UNIT
		16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	73	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	36.1	°C/W
R _{0JB}	Junction-to-board thermal resistance	40.4	°C/W
ΨЈТ	Junction-to-top characterization parameter	17	°C/W
ΨЈВ	Junction-to-board characterization parameter	39.9	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	_	°C/W

For more information about traditional and new thermal metrics, see the no.



5.5 Package Characteristics

	PARAMETER	TEST CONDITIONS	VALUE DBQ-16	UNIT
CLR	External clearance ⁽¹⁾	Side 1 to side 2 distance through air	>3.7	mm
CPG	External creepage ⁽¹⁾	Side 1 to side 2 distance across package surface	>3.7	mm
СТІ	Comparative tracking index	IEC 60112; UL 746A	>600	V
	Material group	According to IEC 60664-1	I	
C _{IO}	Barrier capacitance, input to output ⁽²⁾	$V_{IO} = 0.4 \text{ x sin } (2\pi \text{ft}), f = 1\text{MHz}$	≅1	pF
R _{IO}	Isolation resistance ⁽²⁾	T _A = 25°C	>10 ¹²	Ω

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed-circuit board are used to help increase these specifications.
- (2) All pins on each side of the barrier tied together creating a two-terminal device.



5.6 Electrical Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

001 0	02	1 0	,		
	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -4mA; See Section 6	V _{CCO} - 0.4 (1)		V
V _{OL}	Low-level output voltage	I _{OH} = 4mA; See Section 6		0.4	V
V _{IT+(IN)}	Rising input switching threshold			0.7 × V _{CCI} (1)	V
V _{IT-(IN)}	Falling input switching threshold		0.3 × V _{CCI}		V
V _{I(HYS)}	Input threshold voltage hysteresis		0.1 × V _{CCI}		V
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at INx		10	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at INx	-10		μA
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at ENx		28	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at ENx	-28		μA
CMTI	Common mode transient immunity	V _I = V _{CC} or 0 V, V _{CM} = 1200 V; See Section 6	100	150	kV/μA
Ci	Input Capacitance (2)	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi ft), f = 2$ MHz, $V_{CC} = 5 \text{ V}$		2.8	pF

 $[\]begin{array}{ll} \hbox{(1)} & V_{CCI} = Input\text{-side } V_{CC}; \, V_{CCO} = Output\text{-side } V_{CC} \\ \hbox{(2)} & Measured from input pin to same side ground. \\ \end{array}$



5.7 Supply Current Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO6540							
	$V_I = V_{CC1}$ (1)(ISO6540); $V_I = 0 \text{ V (ISO}$	06540 with F	I _{CC1}		1.6	2.4	
Supply current - DC signal	suffix)		I _{CC2}		2.1	3.7	
(2)	$ V_1 = 0 V $ (ISO6540); $ V_1 = V_{CC1} $ (ISO6540 with F suffix)		I _{CC1}		5.8	8	
			I _{CC2}		2.3	4.0	
		1 Mbps	I _{CC1}		3.7	5.1	mA
		1 Mbps	I _{CC2}		2.4	4.1	ША
Supply current - AC signal	All channels switching with square	10 Mbps	I _{CC1}		3.8	5.3	
(3)	wave clock input; C _L = 15 pF	TO Mibbs	I _{CC2}		4.8	6.6	
		50 Mbps	I _{CC1}		4.4	6	
		50 Mbps	I _{CC2}	,	15	18.1	
ISO6541							
Supply current - DC signal	$V_I = V_{CCI}$ (1)(ISO6541); $V_I = 0 \text{ V}$ (ISO6541 with F suffix)		I _{CC1}		1.9	2.9	
			I _{CC2}		2.2	3.8	
	V _I = 0 V (ISO6541); V _I = V _{CCI} (ISO6541 with F suffix)		I _{CC1}		5.1	7.2	
			I _{CC2}		3.4	5.2	
		1 Mbps	I _{CC1}		3.6	5.1	mA
			I _{CC2}		3	4.7	IIIA
Supply current - AC signal	All channels switching with square	10 Mbps	I _{CC1}		4.2	5.8	
(3)	wave clock input; C _L = 15 pF		I _{CC2}		4.8	6.5	
		FO Mbno	I _{CC1}		7.3	9.3	
		50 Mbps	I _{CC2}		12.6	15.3	
ISO6542							
Supply current - DC	V _I = V _{CCI} ⁽¹⁾ (ISO6542); V _I = 0 V (ISO	6542 with F suffix)	I _{CC1} , I _{CC2}		2.2	3.5	
signal (2)	V _I = 0 V (ISO6542); V _I = V _{CCI} (ISO6542 with F suffix)		I _{CC1} , I _{CC2}		4.4	6.3	
		1 Mbps	I _{CC1,} I _{CC2}		3.4	5	mA
Supply current - AC signal ⁽³⁾	All channels switching with square wave clock input; C ₁ = 15 pF	10 Mbps	I _{CC1} , I _{CC2}		4.7	6.4	
, .g.		50 Mbps	I _{CC1} , I _{CC2}		10.2	12.5	

 ⁽¹⁾ V_{CCI} = Input-side V_{CC}
 (2) Supply current valid for ENx = V_{CCx} and ENx = 0V
 (3) Supply current valid for ENx = V_{CCx}



5.8 Electrical Characteristics—3.3-V Supply

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
High-level output voltage	I _{OH} = -2mA; See Section 6	V _{CCO} - 0.2 (1)		V
Low-level output voltage	I _{OH} = 2mA; See Section 6		0.2	2 V
Rising input switching threshold			0.7 × V _{CCI} ⁽¹) V
Falling input switching threshold		0.3 × V _{CCI}		V
Input threshold voltage hysteresis		0.1 × V _{CCI}		V
High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at INx		10) μΑ
Low-level input current	V _{IL} = 0 V at INx	-10		μA
High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at ENx		30	μΑ
Low-level input current	V _{IL} = 0 V at ENx	-30		μA
Common mode transient immunity	V _I = V _{CC} or 0 V, V _{CM} = 1200 V; See Section 6	100	150	kV/μA
Input Capacitance (2)	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi ft), f = 2$ MHz, $V_{CC} = 3.3 \text{ V}$		2.8	pF
	High-level output voltage Low-level output voltage Rising input switching threshold Falling input switching threshold Input threshold voltage hysteresis High-level input current Low-level input current High-level input current Common mode transient immunity	High-level output voltage I_{OH} = -2mA; See Section 6 Low-level output voltage I_{OH} = 2mA; See Section 6 Rising input switching threshold Falling input switching threshold Input threshold voltage hysteresis High-level input current $V_{IH} = V_{CCI}$ (1) at INx Low-level input current V_{IL} = 0 V at INx High-level input current $V_{IH} = V_{CCI}$ (1) at ENx Low-level input current V_{IL} = 0 V at ENx Common mode transient immunity $V_I = V_{CC}$ or 0 V, V_{CM} = 1200 $V_I = V_{CCI}$ (2 + 0.4×sin(2πft), f = 2	High-level output voltage I_{OH} = -2mA; See Section 6 V_{CCO} - 0.2 (1) Low-level output voltage I_{OH} = 2mA; See Section 6 Rising input switching threshold 0.3 × V_{CCI} Input threshold voltage hysteresis 0.1 × V_{CCI} High-level input current V_{IH} = V_{CCI} (1) at INx Low-level input current V_{IL} = 0 V at INx High-level input current V_{IL} = 0 V at ENx Low-level input current V_{IL} = 0 V at ENx Common mode transient immunity V_I = V_{CC} or 0 V, V_{CM} = 1200 V; See Section 6 Input Canacitance (2) V_I = V_{CC} / 2 + 0.4×sin(2πft), f = 2	High-level output voltage I_{OH} = -2mA; See Section 6 V_{CCO} - 0.2 (1) Low-level output voltage I_{OH} = 2mA; See Section 6 0.2 Rising input switching threshold 0.7 × V_{CCI} (1) Falling input switching threshold 0.3 × V_{CCI} 0.1 × V_{C

 V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} Measured from input pin to same side ground.



5.9 Supply Current Characteristics—3.3-V Supply

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN TY	P MAX	UNIT
ISO6540						
	V _I = V _{CC1} ⁽¹⁾ (ISO6540); V _I = 0 V (ISO6540 with F		I _{CC1}	1.	6 2.3	
Supply current - DC	suffix)			2.	1 3.7	
signal ⁽²⁾	V _I = 0 V (ISO6540); V _I = V _{CC1} (ISO6	540 with E ouffix)	I _{CC1}	5.	7 8	
	V ₁ = 0 V (1300340), V ₁ = V _{CC1} (1300	540 Willi F Sullix)	I _{CC2}	2.	3 4.0	
	1	1 Mbps	I _{CC1}	3.	7 5.1	mA
		1 Mbps	I _{CC2}	2.	4 4.0	IIIA
Supply current - AC	t - AC All channels switching with square wave clock input; C _L = 15 pF	10 Mbps	I _{CC1}	3.	8 5.2	
signal (3)		TO Mbps	I _{CC2}		4 5.8	
		EO Mbno	I _{CC1}	4.	2 5.7	
		50 Mbps	I _{CC2}	11.	2 13.8	
ISO6541						
	$V_{I} = V_{CCI}$ (1)(ISO6541); $V_{I} = 0$ V (ISO6541 with F suffix) $V_{I} = 0$ V (ISO6541); $V_{I} = V_{CCI}$ (ISO6541 with F suffix)		I _{CC1}	1.	9 2.9	
Supply current - DC signal			I _{CC2}	2.	2 3.7	
(2)			I _{CC1}		5 7.1	
			I _{CC2}	3.	4 5.1	
		4 Milese	I _{CC1}	3.	5 5	A
		1 Mbps	I _{CC2}	2.	9 4.6	mA
Supply current - AC signal	All channels switching with square	10 Mbno	I _{CC1}		4 5.5	
(3)	wave clock input; C _L = 15 pF	10 Mbps	I _{CC2}	4.	2 5.9	
		EO Mbno	I _{CC1}	6.	1 8	
		50 Mbps	I _{CC2}	9.	7 12.1	
ISO6542		•				
Supply current - DC	V _I = V _{CCI} ⁽¹⁾ (ISO6542); V _I = 0 V (ISO	6542 with F suffix)	I _{CC1} , I _{CC2}	2.	2 3.4	
signal (2)	V _I = 0 V (ISO6542); V _I = V _{CCI} (ISO65	V _I = 0 V (ISO6542); V _I = V _{CCI} (ISO6542 with F suffix)		4.	4 6.3	
		1 Mbps	I _{CC1,} I _{CC2}	3.	4 4.9	mA
Supply current - AC signal ⁽³⁾	All channels switching with square wave clock input; $C_1 = 15 \text{ pF}$	10 Mbps	I _{CC1} , I _{CC2}	4.	2 5.9	
oignai · ·	wave clock input; $C_L = 15 \text{ pF}$ 50 Mbps		I _{CC1} , I _{CC2}	8.	2 10.3	

 ⁽¹⁾ V_{CCI} = Input-side V_{CC}
 (2) Supply current valid for ENx = V_{CCx} and ENx = 0V
 (3) Supply current valid for ENx = V_{CCx}



5.10 Electrical Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1mA; See Section 6	V _{CCO} - 0.1 ⁽¹⁾			V
V _{OL}	Low-level output voltage	I _{OL} = 1mA; See Section 6			0.1	V
V _{IT+(IN)}	Rising input switching threshold				0.7 × V _{CCI} (1)	V
V _{IT-(IN)}	Falling input switching threshold		0.3 × V _{CCI}			V
V _{I(HYS)}	Input threshold voltage hysteresis		0.1 × V _{CCI}			V
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at INx			10	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at INx	-10			μA
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at ENx			30	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at ENx	-30			μA
CMTI	Common mode transient immunity	V _I = V _{CC} or 0 V, V _{CM} = 1200 V; See Section 6	100	150		kV/µA
Ci	Input Capacitance (2)	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi ft), f = 2$ MHz, $V_{CC} = 2.5 \text{ V}$		2.8		pF

⁽¹⁾ V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} (2) Measured from input pin to same side ground.



5.11 Supply Current Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO6540						·	
	V _I = V _{CC1} ⁽¹⁾ (ISO6540); V _I = 0 V (ISO6540 with F		I _{CC1}		1.6	2.3	
Supply current - DC signal	suffix)		I _{CC2}		2.1	3.7	
(2)	$V_{I} = 0 \text{ V (ISO6540)}; V_{I} = V_{CC1} \text{ (ISO6}$	540 with E suffix)	I _{CC1}		5.7	7.9	
	V = 0 V (1880340), V = V881 (1880		I _{CC2}		2.3	4.0	
	1 Mbps	1 Mhns	I _{CC1}		3.7	5.1	mA
		1 Wibps	I _{CC2}		2.3	4.0	ША
Supply current - AC	All channels switching with square wave clock input; C _L = 15 pF	10 Mbps	I _{CC1}		3.7	5.1	
signal (3)		TO WIDPS	I _{CC2}		3.5	5.3	
		50 Mbps	I _{CC1}		4.1	5.6	
		30 Minhs	I _{CC2}		9	11.5	
ISO6541							
	$V_I = V_{CCI}$ (1)(ISO6541); $V_I = 0$ V (ISO6541 with F suffix) $V_I = 0$ V (ISO6541); $V_I = V_{CCI}$ (ISO6541 with F suffix)		I _{CC1}		1.9	2.9	
Supply current - DC signal			I _{CC2}		2.2	3.7	
(2)			I _{CC1}		5	7.1	
			I _{CC2}		3.4	5.1	
		1 Mbps	I _{CC1}		3.5	5	mA
		1 Mbps	I _{CC2}		2.9	4.5	ША
Supply current - AC signal	All channels switching with square	10 Mbps	I _{CC1}		3.9	5.4	
(3)	wave clock input; C _L = 15 pF	TO MDPS	I _{CC2}		3.8	5.5	
		50 Mbps	I _{CC1}		5.5	7.2	
		30 Mbps	I _{CC2}		8.1	10.2	
ISO6542							
Supply current - DC signal	V _I = V _{CCI} ⁽¹⁾ (ISO6542); V _I = 0 V (ISC	6542 with F suffix)	I _{CC1} , I _{CC2}		2.2	3.4	
(2)	V _I = 0 V (ISO6542); V _I = V _{CCI} (ISO65	542 with F suffix)	I _{CC1} , I _{CC2}		4.3	6.3	
		1 Mbps	I _{CC1,} I _{CC2}		3.3	4.8	mA
Supply current - AC signal (3)	All channels switching with square wave clock input; C _I = 15 pF	10 Mbps	I _{CC1,} I _{CC2}		4	5.6	
3	inate state input, of	50 Mbps	I _{CC1} , I _{CC2}		7	9	

 ⁽¹⁾ V_{CCI} = Input-side V_{CC}
 (2) Supply current valid for ENx = V_{CCx} and ENx = 0V
 (3) Supply current valid for ENx = V_{CCx}



5.12 Electrical Characteristics—1.8-V Supply

 $V_{CC1} = V_{CC2} = 1.8 \text{ V} \pm 5\%$ (over recommended operating conditions unless otherwise noted)

001 0	O2 (1 0	,		
	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1mA; See Section 6	V _{CCO} - 0.1 ⁽¹⁾		V
V _{OL}	Low-level output voltage	I _{OL} = 1mA; See Section 6		0.1	V
V _{IT+(IN)}	Rising input switching threshold			0.7 × V _{CCI} (1)	V
V _{IT-(IN)}	Falling input switching threshold		0.3 × V _{CCI}		V
V _{I(HYS)}	Input threshold voltage hysteresis		0.1 × V _{CCI}		V
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at INx		10	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at INx	-10		μA
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at ENx		30	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at ENx	-30		μA
CMTI	Common mode transient immunity	V _I = V _{CC} or 0 V, V _{CM} = 1200 V; See Section 6	100	150	kV/μA
C _i	Input Capacitance (2)	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi ft), f = 2$ MHz, $V_{CC} = 1.8 \text{ V}$		2.8	pF

 $[\]begin{array}{ll} \hbox{(1)} & V_{CCI} = Input\text{-side } V_{CC}; \, V_{CCO} = Output\text{-side } V_{CC} \\ \hbox{(2)} & Measured from input pin to same side ground. \\ \end{array}$



5.13 Supply Current Characteristics—1.8-V Supply

 $V_{CC1} = V_{CC2} = 1.8 \text{ V} \pm 5\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
ISO6540						'	
	V _I = V _{CC1} ⁽¹⁾ (ISO6540); V _I = 0 V (ISO6540 with F		I _{CC1}		1.2	1.8	
Supply current - DC	suffix)		I _{CC2}		2	3.7	
signal (2)	V _I = 0 V (ISO6540); V _I = V _{CC1} (ISO6	540 with E ouffix)	I _{CC1}		5.1	7.6	
	V ₁ = 0 V (1300340), V ₁ = V _{CC1} (1300	1540 WILLI F SUIIIX)	I _{CC2}		2.2	4.0	
	1 Mbps	1 Mbps	I _{CC1}		3.1	4.7	mA
		1 Mbps	I _{CC2}		2.2	4.0	ША
Supply current - AC	All channels switching with square wave clock input; C _L = 15 pF	10 Mbps	I _{CC1}		3.2	4.8	
signal (3)		10 Mbps	I _{CC2}		3.1	4.9	
		50 Mbps	I _{CC1}		3.4	5.1	
		30 Mbbs	I _{CC2}		7	9.7	
ISO6541							
	$V_I = V_{CCI}$ (1)(ISO6541); $V_I = 0$ V (ISO6541 with F suffix) $V_I = 0$ V (ISO6541); $V_I = V_{CCI}$ (ISO6541 with F suffix)		I _{CC1}		1.5	2.5	
Supply current - DC signal			I _{CC2}		2	3.6	
(2)			I _{CC1}		4.5	6.9	
			I _{CC2}		3.2	5	
		1 Mbps	I _{CC1}		3.1	4.7	mA
		Тибра	I _{CC2}		2.7	4.4	ША
Supply current - AC signal	All channels switching with square	10 Mbps	I _{CC1}		3.3	5	
(3)	wave clock input; C _L = 15 pF	10 Mbps	I _{CC2}		3.4	5.1	
		50 Mbps	I _{CC1}		4.5	6.3	
		30 Mbps	I _{CC2}		6.4	8.7	
ISO6542							
Supply current - DC	$V_I = V_{CCI}$ (1)(ISO6542); $V_I = 0$ V (ISO	06542 with F suffix)	I _{CC1} , I _{CC2}		1.9	3.2	
signal ⁽²⁾	V _I = 0 V (ISO6542); V _I = V _{CCI} (ISO65	542 with F suffix)	I _{CC1} , I _{CC2}		4	6.1	
		1 Mbps	I _{CC1,} I _{CC2}		3	4.7	mA
Supply current - AC signal ⁽³⁾	All channels switching with square wave clock input; $C_1 = 15 \text{ pF}$	10 Mbps	I _{CC1,} I _{CC2}		3.5	5.2	
5		50 Mbps	I _{CC1} , I _{CC2}		5.6	7.6	1

 ⁽¹⁾ V_{CCI} = Input-side V_{CC}
 (2) Supply current valid for ENx = V_{CCx} and ENx = 0V
 (3) Supply current valid for ENx = V_{CCx}



5.14 Switching Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	at 100kbps		11	18	ns
PWD	Pulse width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	See Section 6		0.2	7	ns
t _{sk(o)}	Channel-to-channel output skew time(2)	Same-direction channels			6	ns
t _{sk(pp)}	Part-to-part skew time ⁽³⁾				6	ns
t _r	Output signal rise time	See Section 6		2.6	4.5	ns
t _f	Output signal fall time	See Section 6		2.6	4.5	ns
t _{PHZ}	Disable propagation delay, high-to-high impedance output			18.6	25.8	ns
t _{PLZ}	Disable propagation delay, low-to-high impedance output			18.6	25.8	ns
t _{PZH}	Enable propagation delay, high impedance-to-high output for ISO654x	See Section 6		14.2	21.1	ns
t _{PZL}	Enable propagation delay, high impedance-to-low output for ISO654x			14.2	21.1	ns
t _{PU}	Time from UVLO to valid output data				300	μs
t _{DO}	Default output delay time from input power loss	Measured from the time VCC goes below 1.2V. See Section 6		0.1	0.3	μs
t _{ie}	Time interval error	2 ¹⁶ – 1 PRBS data at 50 Mbps		1		ns

⁽¹⁾ Also known as pulse skew.

⁽²⁾ $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

⁽³⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.



5.15 Switching Characteristics—3.3-V Supply

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	at 100kbps		11	18	ns
PWD	Pulse width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	See Figure 1-1		0.5	7	ns
t _{sk(o)}	Channel-to-channel output skew time(2)	Same-direction channels			6	ns
t _{sk(pp)}	Part-to-part skew time ⁽³⁾				7	ns
t _r	Output signal rise time	See Section 6		1.6	3.2	ns
t _f	Output signal fall time	See Section 6		1.6	3.2	ns
t _{PHZ}	Disable propagation delay, high-to-high impedance output			23.2	34.4	ns
t _{PLZ}	Disable propagation delay, low-to-high impedance output			23.2	34.4	ns
t _{PZH}	Enable propagation delay, high impedance-to-high output for ISO654x	See Section 6		16.6	23	ns
t _{PZL}	Enable propagation delay, high impedance-to-low output for ISO654x			16.6	23	ns
t _{PU}	Time from UVLO to valid output data				300	μs
t _{DO}	Default output delay time from input power loss	Measured from the time VCC goes below 1.2V. See Section 6		0.1	0.3	μs
t _{ie}	Time interval error	2 ¹⁶ – 1 PRBS data at 50 Mbps		1		ns

⁽¹⁾ Also known as pulse skew.

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⁽²⁾ t_{sk(o)} is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

⁽³⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.



5.16 Switching Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	at 100kbps		12	20.5	ns
PWD	Pulse width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	See Figure 1-1		0.6	7.1	ns
t _{sk(o)}	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			6	ns
t _{sk(pp)}	Part-to-part skew time ⁽³⁾				7	ns
t _r	Output signal rise time	See Section 6		2	4	ns
t _f	Output signal fall time	See Section 6		2	4	ns
t _{PHZ}	Disable propagation delay, high-to-high impedance output			28.1	43	ns
t _{PLZ}	Disable propagation delay, low-to-high impedance output			28.1	43	ns
t _{PZH}	Enable propagation delay, high impedance-to-high output for ISO654x	See Section 6		20.4	36.3	ns
t _{PZL}	Enable propagation delay, high impedance-to-low output for ISO654x			20.4	36.3	ns
t _{PU}	Time from UVLO to valid output data				300	μs
t _{DO}	Default output delay time from input power loss	Measured from the time VCC goes below 1.2V. See Section 6		0.1	0.3	μs
t _{ie}	Time interval error	2 ¹⁶ – 1 PRBS data at 50 Mbps		1		ns

⁽¹⁾ Also known as pulse skew.

⁽²⁾ $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

⁽³⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.



5.17 Switching Characteristics—1.8-V Supply

 $V_{CC1} = V_{CC2} = 1.8 \text{ V} \pm 5\%$ (over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	at 100kbps		15	24	ns
PWD	Pulse width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	See Figure 1-1		0.7	8.2	ns
t _{sk(o)}	Channel-to-channel output skew time(2)	Same-direction channels			6	ns
t _{sk(pp)}	Part-to-part skew time ⁽³⁾				8.8	ns
t _r	Output signal rise time	See Section 6		2.7	5.3	ns
t _f	Output signal fall time	See Section 6		2.7	5.3	ns
t _{PHZ}	Disable propagation delay, high-to-high impedance output			40.3	63	ns
t _{PLZ}	Disable propagation delay, low-to-high impedance output			40.3	63	ns
t _{PZH}	Enable propagation delay, high impedance-to-high output for ISO654x	See Section 6		30	51.4	ns
t _{PZL}	Enable propagation delay, high impedance-to-low output for ISO654x			30	51.4	ns
t _{PU}	Time from UVLO to valid output data				300	μs
t _{DO}	Default output delay time from input power loss	Measured from the time VCC goes below 1.2V. See Section 6		0.1	0.3	μs
t _{ie}	Time interval error	2 ¹⁶ – 1 PRBS data at 50 Mbps		1		ns

⁽¹⁾ Also known as pulse skew.

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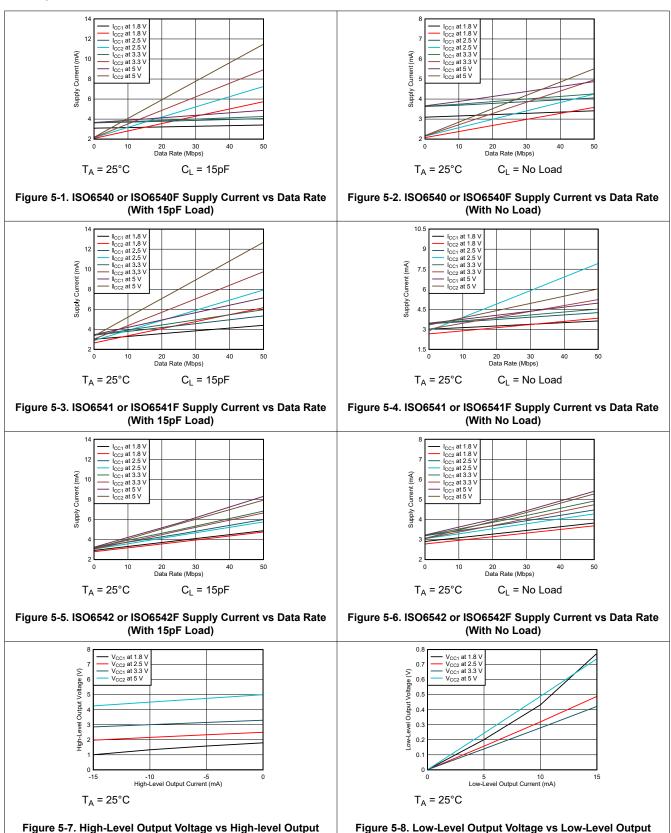
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⁽²⁾ t_{sk(o)} is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

⁽³⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.



5.18 Typical Characteristics



Current

Current



5.18 Typical Characteristics (continued)

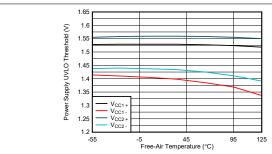


Figure 5-9. Power Supply Undervoltage Threshold vs Free-Air Temperature

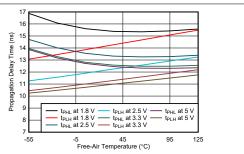
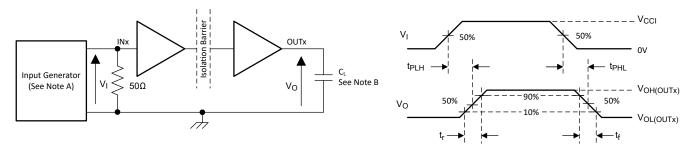


Figure 5-10. Propagation Delay Time vs Free-Air Temperature

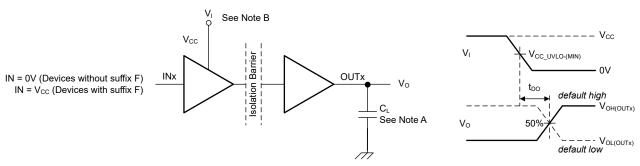


6 Parameter Measurement Information



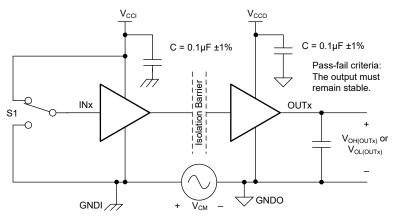
- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50kHz, 50% duty cycle, $t_r \leq$ 3ns, $t_f \leq$ 3ns, $Z_O = 50\Omega$. At the input, 50Ω resistor is required to terminate INx (input) generator signal. The 50Ω resistor is not needed in the actual application.
- B. C_L = 15pF and includes instrumentation and fixture capacitance within ±20%.

Figure 6-1. Switching Characteristics Test Circuit and Voltage Waveforms



- A. $C_L = 15$ pF and includes instrumentation and fixture capacitance within ±20%.
- B. Power Supply Ramp Rate = 10mV/ns

Figure 6-2. Default Output Delay Time Test Circuit and Voltage Waveforms



- A. C_L = 15pF and includes instrumentation and fixture capacitance within ±20%.
- B. $ENx = V_{CC}$, channels are enabled during CMTI test.

Figure 6-3. Common-Mode Transient Immunity Test Circuit



7 Detailed Description

7.1 Overview

The ISO654x family of devices have an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon dioxide based isolation barrier.

The transmitter sends a high frequency carrier across the barrier to represent one digital state and sends no signal to represent the other digital state. The receiver demodulates the signal after advanced signal conditioning and produces the output through a buffer stage. The ISO654x devices also incorporate advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions due to the high frequency carrier and IO buffer switching.

7.2 Functional Block Diagram

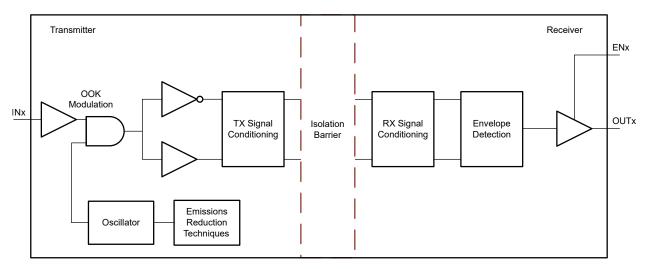


Figure 7-1. Conceptual Block Diagram of an OOK Based Digital Isolator

Figure 7-2 shows a conceptual detail of how the ON-OFF keying scheme works.

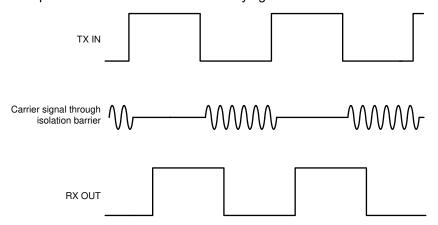


Figure 7-2. On-Off Keying (OOK) Based Modulation Scheme

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7.3 Feature Description

Table 7-1 provides an overview of the device features.

Table 7-1. Device Features

PART NUMBER	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT	PACKAGE
ISO6540	4 Forward 0 Reverse	50Mbps	High	DBQ-16
ISO6540F	4 Forward 0 Reverse	50Mbps	Low	DBQ-16
ISO6541	3 Forward 1 Reverse	50Mbps	High	DBQ-16
ISO6541F	3 Forward 1 Reverse	50Mbps	Low	DBQ-16
ISO6542	2 Forward 2 Reverse	50Mbps	High	DBQ-16
ISO6542F	2 Forward 2 Reverse	50Mbps	Low	DBQ-16

7.3.1 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are defined and tested by international standards such as IEC 61000-4-x and CISPR 32. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO654x family of devices incorporates many chip-level design techniques to help overall system robustness.

7.4 Device Functional Modes

Table 7-2 lists the functional modes for the ISO654x devices.

Table 7-2. Function Table

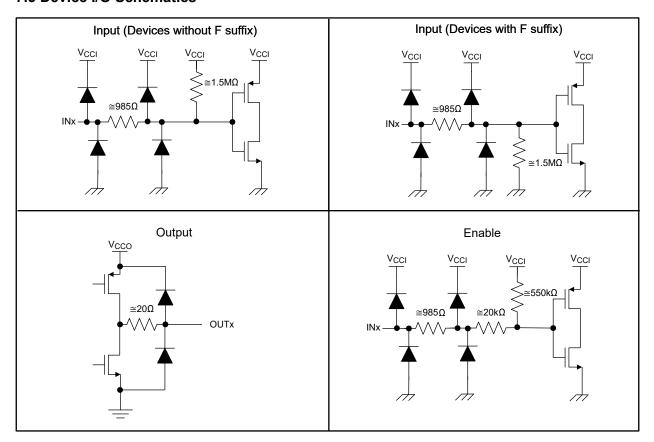
Table 1 all allocation table						
V _{cco}	INPUT (INx)	OUTPUT ENABLE (ENx)	OUTPUT (OUTx)	COMMENTS		
	Н	H or open	Н	Normal Operation: A channel output assumes the logic state of the		
	L	H or open	L	input.		
PU	Open	H or open	Default	Default mode: When INx is open, the corresponding channel output goes to the default logic state. Default is <i>High</i> for ISO654x and <i>Low</i> for ISO654xF (with F suffix).		
PU	Х	L	Z	A low value of output enable causes the outputs to be high-impedance.		
PU	х	H or open	Default	Default mode: When V_{CCI} is unpowered, a channel output assumes the logic state based on the selected default option. Default is \textit{High} for ISO654x and \textit{Low} for ISO654xF (with F suffix). When V_{CCI} transitions from unpowered to powered-up, a channel output assumes the logic state of the input. When V_{CCI} transitions from powered-up to unpowered, channel output assumes the selected default state.		
PD	Х	Х	Undetermined	When $V_{\rm CCO}$ is unpowered, a channel output is undetermined ⁽²⁾ . When $V_{\rm CCO}$ transitions from unpowered to powered-up, a channel output assumes the logic state of the input.		
	PU PU	Vcco (INx) H L Open X	Vcco INPUT (INx) ENABLE (ENx) H H or open L H or open Open H or open PU X L H or open H or open H or open	Vcco INPUT (INx) ENABLE (ENx) OUTPUT (OUTx) H H or open H L H or open L PU X L Z PU X H or open Default		

⁽¹⁾ V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}; PU = Powered up (V_{CC} ≥ V_{CC_RO(MIN)}); PD = Powered down (V_{CC} ≤ V_{CC_UVLO}-); X = Irrelevant; H = High level; L = Low level; Z = High Impedance

⁽²⁾ The outputs are in undetermined state when $V_{CC\ UVLO-} \le V_{CCI}$ or $V_{CCO} < V_{CC} \ge V_{CC\ RO(MIN)}$



7.5 Device I/O Schematics





8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The ISO654x devices are high-performance, low power, quad-channel digital isolators. These devices come with enable pins on each side which can be used to put the respective outputs in high impedance for parallel (multiple) driver applications. The ISO654x devices use single-ended CMOS-logic switching technology.

The supply voltage range is from 1.71V to 5.5V for both supplies, V_{CC1} and V_{CC2} . Since an isolation barrier separates the two sides, each side can be sourced independently with any voltage within recommended operating conditions. As an example, supplying ISO654x V_{CC1} with 3.3V (which is within1.71V to 5.5V) and V_{CC2} with 5V (which is also within 1.71V to 5.5V) is possible. You can use the digital isolator as a logic-level translator in addition to providing isolation. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is, MCU or FPGA), and a data converter or a line transceiver, regardless of the interface type or standard.

Note

ISO654x is a functional isolator, and is not certified for isolation by standard bodies. For applications that require certified isolation by standard bodies, customers must choose ISO644x, ISO674x, ISO774x or ISO784x families of digital isolators.

8.2 Typical Application

Figure 8-1 shows the isolated serial peripheral interface (SPI).

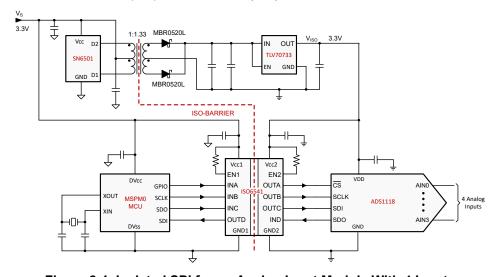


Figure 8-1. Isolated SPI for an Analog Input Module With 4 Inputs



8.2.1 Design Requirements

To design with these devices, use the parameters listed in Table 8-1.

Table 8-1. Design Parameters

PARAMETER	VALUE
Supply voltage, V _{CC1} and V _{CC2}	1.71V to 5.5V
Decoupling capacitor between V _{CC1} and GND1	0.1µF
Decoupling capacitor from V _{CC2} and GND2	0.1μF

8.2.2 Detailed Design Procedure

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the ISO654x family of devices only require two external bypass capacitors to operate.

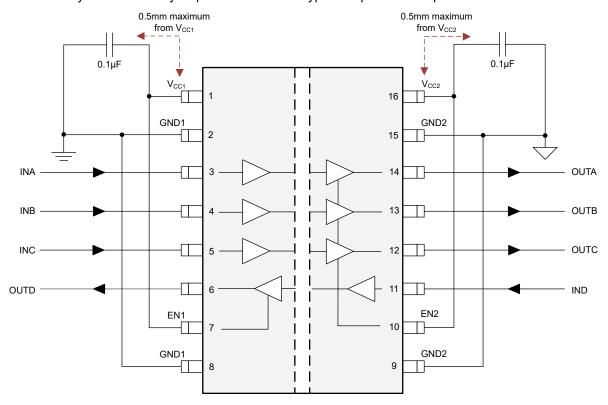
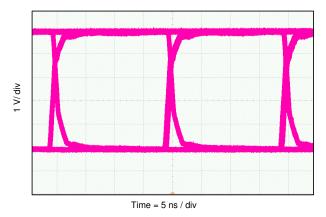


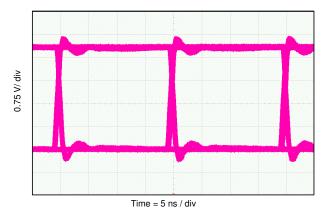
Figure 8-2. Typical ISO654x Circuit

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8.2.3 Application Curve

The following typical eye diagrams of the ISO654x family of devices indicates low jitter and wide open eye at the maximum data rate of 50Mbps.



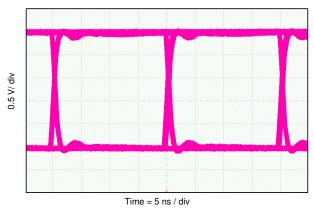


Horizontal 5ns / division, Vertical 1V / division.

Horizontal 5ns / division, Vertical 750mV / division.

Figure 8-3. ISO654x Eye Diagram at 50Mbps PRBS F 2¹⁶ – 1, 5V and 25°C

Figure 8-4. ISO654x Eye Diagram at 50Mbps PRBS 2¹⁶ – 1, 3.3V and 25°C



Horizontal 5ns / division, Vertical 500mV / division.

Figure 8-5. ISO654x Eye Diagram at 50Mbps PRBS 2¹⁶ - 1, 2.5V and 25°C



8.3 Power Supply Recommendations

To provide reliable operation at data rates and supply voltages, a $0.1\mu F$ bypass capacitor is recommended at the input and output supply pins (V_{CC1} and V_{CC2}). The capacitors must be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver. For industrial applications, please use Texas Instruments' SN6501 or SN6505B. For such applications, detailed power supply design and transformer selection recommendations are available in SN6501 Transformer Driver for Isolated Power Supplies or SN6505B Low-noise, 1-A Transformer Drivers for Isolated Power Supplies .

8.4 Layout

8.4.1 Layout Guidelines

A minimum of two layers is required to accomplish a cost optimized and low EMI PCB design. To further improve EMI, a four layer board can be used (see Layout Example Schematic). Layer stacking for a four layer board must be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of the
 inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits
 of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100pF/inch².
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links typically have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep the planes symmetrical. This design makes the stack mechanically stable and prevents warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, refer to the *Digital Isolator Design Guide* application note.

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8.4.2 Layout Example

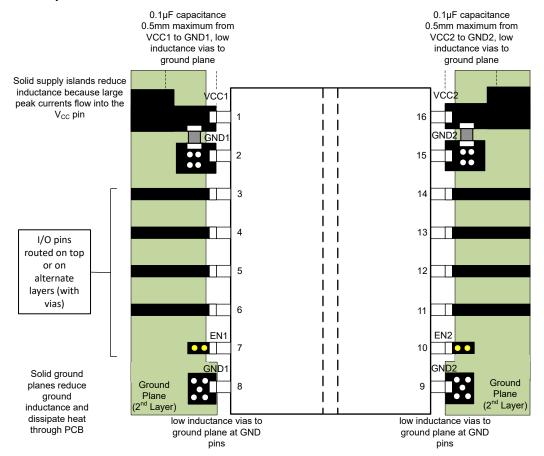


Figure 8-6. Layout Example

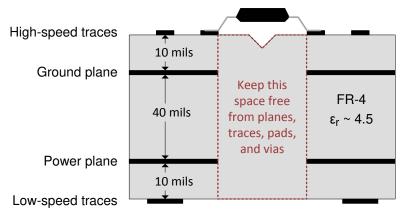


Figure 8-7. Layout Example PCB cross section



9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, ISO6540 Technical Documents
- Texas Instruments, ISO6541 Technical Documents
- Texas Instruments, ISO6542 Technical Documents
- Texas Instruments, Digital Isolator Design Guide, application note
- Texas Instruments, Digital Isolator Design Guide, application note
- · Texas Instruments, Isolation Glossary, application note
- Texas Instruments, How to use isolation to improve ESD, EFT, and Surge immunity in industrial systems, application note
- Texas Instruments, SN6501 Transformer Driver for Isolated Power Supplies, data sheet

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES				
April 2025	*	Initial release				

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
ISO6540DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	6540
ISO6540FDBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	6540F
ISO6540FDBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	See ISO6540FDBQR	6540F
ISO6541DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	6541
ISO6541DBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	See ISO6541DBQR	6541
ISO6541FDBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	6541F
ISO6541FDBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	See ISO6541FDBQR	6541F
ISO6542DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	6542
ISO6542DBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	See ISO6542DBQR	6542
ISO6542FDBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	6542F
ISO6542FDBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	See ISO6542FDBQR	6542F

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF ISO6540, ISO6541, ISO6542:

Automotive: ISO6540-Q1, ISO6541-Q1, ISO6542-Q1

NOTE: Qualified Version Definitions:

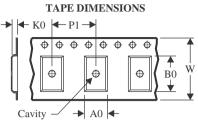
Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

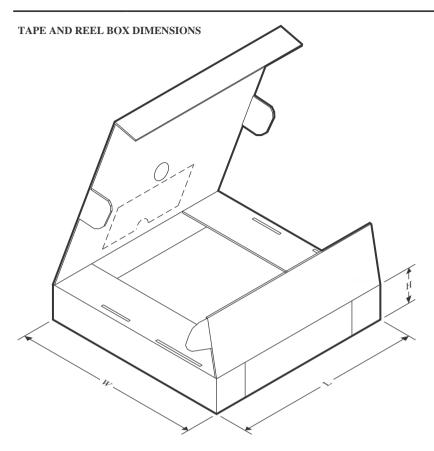


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO6540DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO6540FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO6541DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO6541FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO6542DBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO6542FDBQR	SSOP	DBQ	16	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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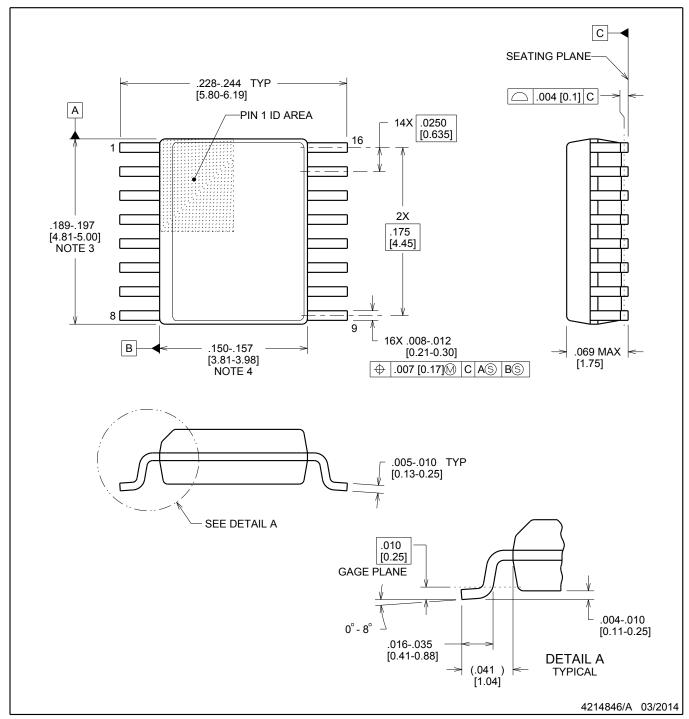


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO6540DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO6540FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO6541DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO6541FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO6542DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
ISO6542FDBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0



SHRINK SMALL-OUTLINE PACKAGE

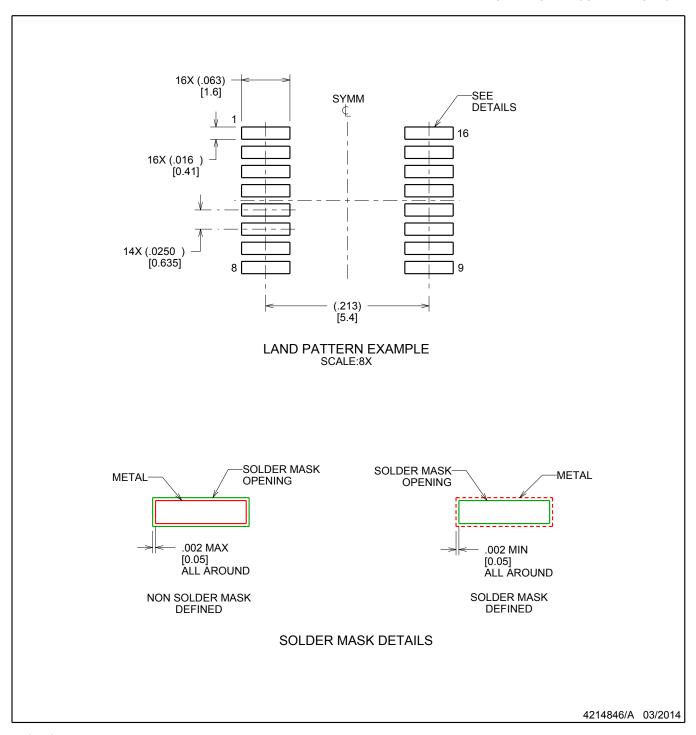


NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MO-137, variation AB.



SHRINK SMALL-OUTLINE PACKAGE



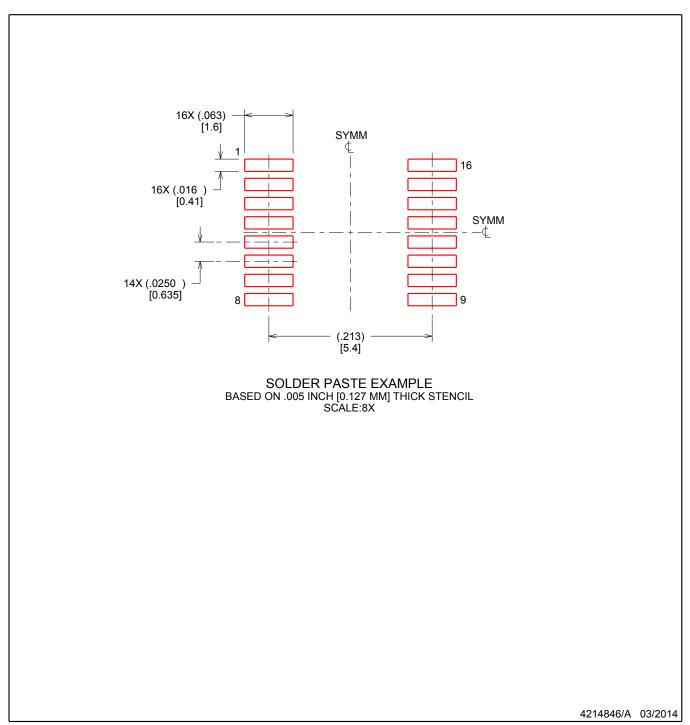
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SHRINK SMALL-OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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